

Schottky Dual Diode

PBYR290CT

90V / 2A

DATASHEET

OEM – Philips

Source: Philips Databook 1999

Schottky barrier double diodes

PBYR2100CT series

FEATURES

- Low switching losses
- High breakdown voltage
- Fast recovery time
- Guard ring protected
- Plastic SMD package.

APPLICATIONS

- Low power, switched-mode power supplies
- Rectification
- Polarity protection.

DESCRIPTION

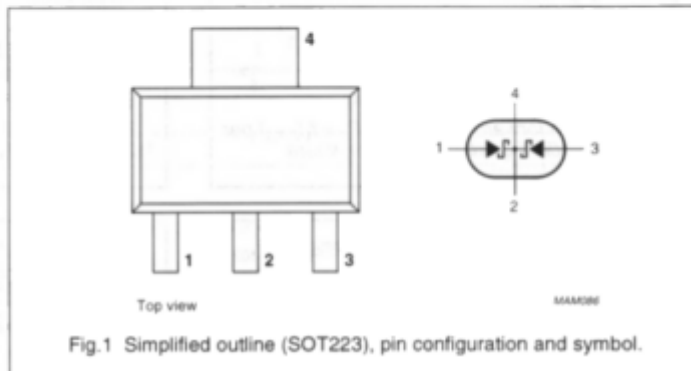
The PBYR2100CT series consists of Schottky barrier double diodes, fabricated in planar technology, and encapsulated in SOT223 plastic SMD packages.

PINNING

PIN	DESCRIPTION
1	anode (a ₁)
2	common cathode
3	anode (a ₂)
4	common cathode

MARKING

TYPE NUMBER	MARKING CODE
PBYR280CT	BYR28
PBYR290CT	BYR29
PBYR2100CT	BYR210



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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_R	continuous reverse voltage				
	PBYR280CT		–	80	V
	PBYR290CT		–	90	V
	PBYR2100CT		–	100	V
V_{RRM}	repetitive peak reverse voltage				
	PBYR280CT		–	80	V
	PBYR290CT		–	90	V
	PBYR2100CT		–	100	V
V_{RWM}	crest working reverse voltage				
	PBYR280CT		–	80	V
	PBYR290CT		–	90	V
	PBYR2100CT		–	100	V
$I_{F(AV)}$	average forward current	$T_{amb} = 85\text{ °C}$; see Fig.2; $R_{th\ j-a} = 70\text{ K/W}$; note 1; $V_{R(equiv)} = 0.2\text{ V}$; note 2	–	1	A
I_{FSM}	non-repetitive peak forward current	$t = 8.3\text{ ms}$ half sine wave; JEDEC method	–	10	A
I_{RSM}	non-repetitive peak reverse current	$t_p = 100\text{ }\mu\text{s}$	–	0.5	A
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–65	+150	°C
T_{amb}	operating ambient temperature		–	85	°C

Notes

1. Refer to SOT223 standard mounting conditions.
2. For Schottky barrier diodes thermal run-away has to be considered, as in some applications, the reverse power losses P_R are a significant part of the total power losses. Nomograms for determination of the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.

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ELECTRICAL CHARACTERISTICS

$T_{amb} = 25\text{ °C}$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per diode						
V_F	forward voltage	see Fig.3 $I_F = 1\text{ A}$; note 1	–	–	790	mV
		$I_F = 1\text{ A}$; $T_J = 100\text{ °C}$; note 1	–	–	690	mV
I_R	reverse current	$V_R = V_{RRMmax}$; note 1; see Fig.4	–	–	0.5	mA
		$V_R = V_{RRMmax}$; $T_J = 100\text{ °C}$; note 1; see Fig.4	–	–	5	mA
C_d	diode capacitance	$V_R = 4\text{ V}$; $f = 1\text{ MHz}$; see Fig.5	–	–	100	pF

Note

1. Pulsed test: $t_p = 300\text{ }\mu\text{s}$; $\delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R_{th-j-a}	thermal resistance from junction to ambient	note 1	70	K/W

Note

1. Refer to SOT223 standard mounting conditions.

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GRAPHICAL DATA

